

Docket No. NEC01P069-MSb

Figures 7a-7b show another example of the conventional method for producing a semiconductor device.

Figures 8a-8b show still another example of the conventional method for producing a semiconductor device.

Figures 9a-9b show still another example of the conventional method of producing a semiconductor device.

Figures 10a-10c show still another example of the method of the present invention for producing a semiconductor device.

Figures 11a-11b show still another example of the of the method of the present invention for producing a semiconductor device.

**IN THE CLAIMS:**

**Please amend the claims as follows:**

15. (Amended) The method of forming a multi-layered insulation film according to claim 9, characterized in that said semiconductor wafer is spin-coated with a solution containing said organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more, and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

23. (Amended) The method of producing a semiconductor device according to claim 16, characterized in that said semiconductor wafer is spin-coated with a solution containing the organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

**Please add the following new claims:**

- - 24. (New) The method of forming a multi-layered insulation film according to claim 10, characterized in that said semiconductor wafer is spin-coated with a solution containing said organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more, and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

25. (New) The method of forming a multi-layered insulation film according to claim 11, characterized in that said semiconductor wafer is spin-coated with a solution containing said organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more, and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

26. (New) The method of forming a multi-layered insulation film according to claim 12, characterized in that said semiconductor wafer is spin-coated with a solution containing said

organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more, and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

27. (New) The method of producing a semiconductor device according to claim 17, characterized in that said semiconductor wafer is spin-coated with a solution containing the organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

28. (New) The method of producing a semiconductor device according to claim 18, characterized in that said semiconductor wafer is spin-coated with a solution containing the organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.

29. (New) The method of producing a semiconductor device according to claim 19, characterized in that said semiconductor wafer is spin-coated with a solution containing the organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more and 500°C or less, inclusive, and coated with said second insulation layer by plasma

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CVD method.

30. (New) The method of producing a semiconductor device according to claim 20, characterized in that said semiconductor wafer is spin-coated with a solution containing the organic material of low dielectric constant and then thermally treated to form said first insulation layer, and said first insulation layer is thermally treated in atmosphere at 200°C or more and 500°C or less, inclusive, and coated with said second insulation layer by plasma CVD method.